

ABSTRACT OF THE DISCLOSURE

A bottom-gate thin-film transistor includes a gate electrode, a gate insulating film, an active layer, and a protective insulating film deposited in that order on a substrate. The protective insulating film has a thickness of 100 nm or less, and the protective insulating film is formed on any one of the active layer, and LDD region, and a source-drain region. A method for making a bottom-gate thin-film transistor, a liquid crystal display device including a TFT substrate using the bottom-gate thin-film transistor and a method for fabricating the same, and an organic EL device including the bottom-gate thin-film transistor and a method for fabricating the same are also disclosed.